

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Won-suk YANG et al.

Group Art Unit: 2814

Application Serial No.: 09/313,659

Examiner: S. Rao

Filed: May 18, 1999

Title: METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE

Assistant Commissioner of Patents  
Washington, D.C. 20231

RESPONSE TO OFFICE ACTION

Sir:

In response to the Office Action dated August 15, 2000, the period for response to which extends through November 15, 2000, please consider the following amendments.

IN THE TITLE:

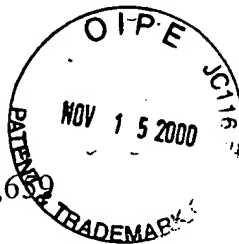
Please cancel the current title and replace it with the following.

--METHOD OF FABRICATING A MOS TRANSISTOR WITH DOUBLE  
SIDEWALL SPACERS IN A PERIPHERAL REGION AND SINGLE SIDEWALL  
SPACERS IN A CELL REGION--.

IN THE SPECIFICATION:

Please amend the specification as follows.

GP 2814  
#6/12  
11-18-00  
SEC. 636  
109/313,659



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